

L Number	Hits	Search Text	DB	Time stamp
1	432	438/96.ccls.	USPAT	2004/09/29 17:33
2	264	438/97.ccls.	USPAT	2004/09/29 17:33
3	682	438/149.ccls.	USPAT	2004/09/29 17:33
4	100	438/150.ccls.	USPAT	2004/09/29 17:34
5	661	438/151.ccls.	USPAT	2004/09/29 17:34
6	641	438/166.ccls.	USPAT	2004/09/29 17:34
7	480	438/479.ccls.	USPAT	2004/09/29 17:34
8	251	438/482.ccls.	USPAT	2004/09/29 17:34
9	385	438/486.ccls.	USPAT	2004/09/29 17:34
10	347	438/487.ccls.	USPAT	2004/09/29 17:34
11	381	438/488.ccls.	USPAT	2004/09/29 17:34
12	83	438/491.ccls.	USPAT	2004/09/29 17:35
13	75	lee-seok\$.in.	USPAT	2004/09/29 17:35
14	91	lee-seok\$.in.	US-PGPUB	2004/09/29 17:35
15	48	lee-seok\$.in.	EPO; JPO; DERWENT; IBM_TDB	2004/09/29 17:35
16	10249	(amorph\$6 and crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)	USPAT	2004/09/29 17:41
17	4160	((amorph\$6 and crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)) and (TFT (thin same transistor))	USPAT	2004/09/29 17:41
18	7700	((amorph\$6 and crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)) and (amorph\$6 same crystal\$9)	USPAT	2004/09/29 17:38
19	3406	(((amorph\$6 and crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)) and (amorph\$6 same crystal\$9)) and (((amorph\$6 and crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)) and (TFT (thin same transistor)))	USPAT	2004/09/29 17:39
20	2675	((((amorph\$6 and crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)) and (amorph\$6 same crystal\$9)) and (((amorph\$6 and crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)) and (TFT (thin same transistor)))) and active	USPAT	2004/09/29 17:39

21	2380	(((amorph\$6 and crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)) and (amorph\$6 same crystal\$9)) and (((amorph\$6 and crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)) and (TFT (thin same transistor)))) and active) and pattern\$6	USPAT	2004/09/29 17:39
22	170	(((amorph\$6 and crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)) and (amorph\$6 same crystal\$9)) and (((amorph\$6 and crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)) and (TFT (thin same transistor)))) and active) and pattern\$6) and (rapid same oxid\$9)	USPAT	2004/09/29 17:40
23	1609	(((amorph\$6 and crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)) and (amorph\$6 same crystal\$9)) and (((amorph\$6 and crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)) and (TFT (thin same transistor)))) and active) and pattern\$6) and pixel	USPAT	2004/09/29 17:41
24	3968	(amorph\$6 same crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)	US-PGPUB	2004/09/29 17:42
25	2062	((amorph\$6 same crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)) and (TFT (thin same transistor))	US-PGPUB	2004/09/29 17:42
26	1451	((amorph\$6 same crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)) and (TFT (thin same transistor)) and pixel	US-PGPUB	2004/09/29 17:42
27	1108	(amorph\$6 same crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)	EPO; JPO; DERWENT; IBM_TDB	2004/09/29 17:42
28	369	((amorph\$6 same crystal\$9) and (anneal\$6 rta rtp rto) and (silicon polysilicon)) and (TFT (thin same transistor))	EPO; JPO; DERWENT; IBM_TDB	2004/09/29 17:42